Constellation-X Hard X-ray Telescope

• Brief overview - Harrison

Detectors

CdZnTe detector resolution and imaging performance - *Harrison* Detector packaging - *Rothschild* EXIST development - relationship to Con-X HXT- *Grindlay*

Optics

Replicated optics - Gorenstein

Replicated optics - *Ulmer*

InFocus optics calibration results - Petre

Production multilayer coating facility results - Christensen

Overview

HXT technology is new. Con-X would be the first significant mission incorporating focusing above ~10 keV

Limited project funding supported:

coating deposition/evaluation at CfA evaluation of new CdZnTe material (GSFC/CIT) formulation of engineering requirements

Significant progress made through individual SR&T efforts

Balloon payloads (HEFT, Infocus, HERO) InFocus test flight measured background in shielded

configuration

No clear hurdles in meeting baseline performance, but performance for full prototypes is yet to be demonstrated

this should happen over next 1 - 2 years

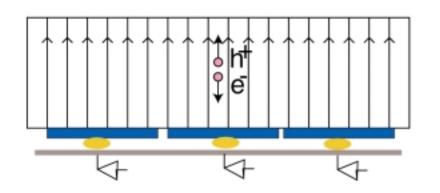
Program funding will be required to bring technologies to TRL 6

Requirements

Baseline HXT Requirements	
Effective Area	$\geq 1500 \text{ cm}^2 \text{ (6 - 40 keV)}$
Signal/Background	$\geq 1 \text{ for } T_{obs} > 2 \times 10^4 \text{ s}$
FOV	\geq 8 arcmin (6 - 40 keV)
Angular resolution	≤ 1 arcmin HPD
ΔΕ/Ε	≤ 20% (6 - 30 keV)
Desirable Performance Enhancements	
Signal/Background	$\geq 1 \text{ for } T_{obs} > 2 \times 10^4 \text{ s}$
Effective Area/	$\geq 1500 \text{ cm}^2 \text{ (6 - 40 keV)}$
Bandpass	extend to 1 keV
Angular resolution	≤ 1 arcmin HPD
ΔΕ/Ε	≤ 5% at 40 keV
Mechanical Envelope	
Total Mass/Satellite	≤ 250 kg
Geometric Aperture	$< 0.75 \text{ m}^2$
Focal Length	10 meters

- Match spectroscopic sensitivity of SXT for high-energy continuum observations
- Map non-thermal emission in extended sources

CdZnTe Pixel Detectors



Selected CdZnTe for sensor

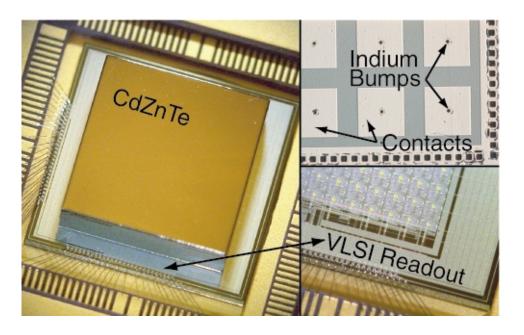
high atomic number wide band gap - no cryogens



Bottom contact (anode) segmented into pixels

Each contact is connected via Indium bump bonding to a separate readout

1-to-1 correspondence between # readout channels and # pixels



Detector Optimization

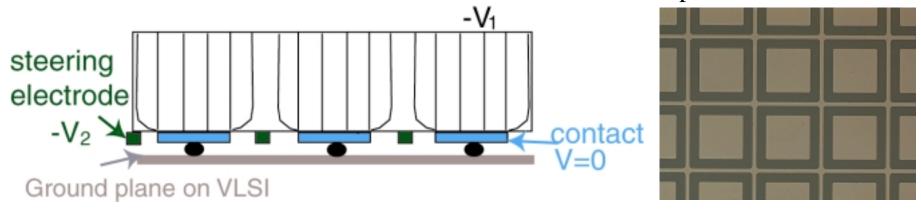
Electrode design

Want to minimize contact size:

reduce capacitance

hole trapping degrades energy resolution - minimized for small pixels

Add steering electrode to avoid charge loss between pixels low-resistivity surface layer has long-lived e⁻ traps



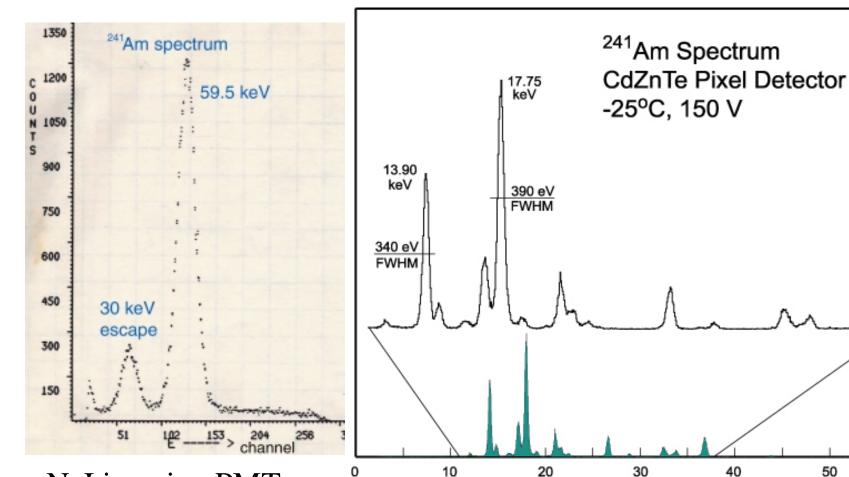
Readout

Custom low-noise circuit implemented in CMOS VLSI technology.

Full circuit through peak sampling in 500 µm²

40 e⁻ rms readout noise (compared to 250 e⁻ for available chips)

HEFT Pixel Detector Performance



NaI imaging PMT 1mm spatial resolution

(Harrison et al. Proc. SPIE 1992)

500 µm CdZnTe detector/VLSI readout

Energy (keV)

40

59.5

keV

550 eV

FWHM

60

50

(Harrison et al. Proc. SPIE 2000)